

Enhancement Mode Gallium Nitride (GaN) HEMT

700 V, 75 mΩ, 21 A, PTFP-N9 (DFN)

NTMT100N70GN1

Features

- Low $R_{DS(ON)}$ to Minimize Conduction Losses
- Ultra Low Gate Charge for High Speed Switching
- $FOM-Q_G = 280 \text{ nC} \cdot \text{m}\Omega$
- Small Footprint for High Density PCB Design
- This Device is Pb-Free, Halide Free and is RoHS Compliant

Typical Applications

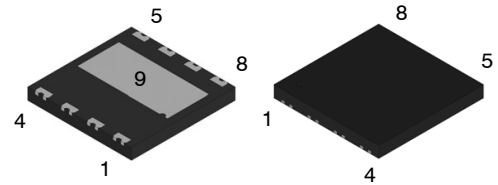
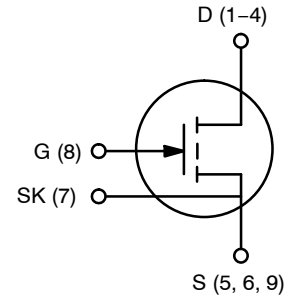
- High Density Power Modules
- High Frequency AC-DC and DC-DC Converters
- High Performance PSU for Consumer and Industrial
- Resonant Conversion

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	700	V
Drain-to-Source Transient Voltage, $t_P < 200 \mu\text{s}$	$V_{DS(TRAN)}$	800	V
Pulsed Drain-to-Source Voltage, $T_J = 25^\circ\text{C}$ ($t_{TOTAL} < 10 \text{ h}$) / $T_J = 125^\circ\text{C}$ ($t_{TOTAL} < 1 \text{ h}$)	$V_{DS(PULSE)}$	750	
Gate-to-Source Voltage	V_{GS}	-6 to 7	V
Gate-to-Source Transient Voltage, $t_P = 50 \text{ ns}$, $f_P = 100 \text{ kHz}$, Open Drain	$V_{GS(PULSE)}$	-20 to 10	V
Continuous Drain Current, $T_{CASE} = 25^\circ\text{C}$	I_{DS}	21	A
Pulsed Drain Current, $t_P < 10 \mu\text{s}$, $T_C = 25^\circ\text{C}$ $T_C = 125^\circ\text{C}$	$I_{DS(PULSE)}$	41 23	A
Power Dissipation, $V_{GS} = 6 \text{ V}$, $T_{CASE} = 25^\circ\text{C}$	P_{TOT}	111	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 to 150	$^\circ\text{C}$

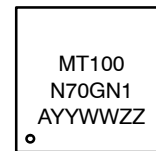
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

$V_{(BR)DSS}$	$R_{DS(ON)}$ TYP	I_{DS} MAX
700 V	75 mΩ	21 A



PTFP-N9 8.00x8.00x0.90, 2.00P
(DFN)
CASE 522AG

MARKING DIAGRAM



MT100N70GN1 = Specific Device Code
 A = Assembly Location
 YY = Year
 WW = Work Week
 ZZ = Assembly Lot Code

ORDERING INFORMATION

Device	Package	Shipping†
NTMT100N70GN1TXG	PTFP-N9 (DFN)	2500 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, [BRD8011/D](http://www.onsemi.com/BRD8011/D).

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THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Junction-to-Case	$R_{\theta JC}$	1.12	$^{\circ}\text{C}/\text{W}$
Junction-to-Ambient (Note 1)	$R_{\theta JA}$	66.4	$^{\circ}\text{C}/\text{W}$
Maximum Soldering Temperature (MSL3)	T_{SLD}	260	$^{\circ}\text{C}$

1. Device on 1 in², 2 oz copper pad on single layer FR-4 PCB.

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}$	700			V
Drain-to-Source Leakage Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 700\text{ V}$		0.8	48	μA
		$V_{GS} = 0\text{ V}, V_{DS} = 700\text{ V}, T_J = 125^{\circ}\text{C}$		9		
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = 6\text{ V}, V_{DS} = 0\text{ V}$		45		μA

ON CHARACTERISTICS

Drain-to-Source On Resistance	$R_{DS(ON)}$	$V_{GS} = 6\text{ V}, I_{DS} = 0.5\text{ A}$		75	100	m Ω
		$V_{GS} = 6\text{ V}, I_{DS} = 6\text{ A}$		75		
		$V_{GS} = 6\text{ V}, I_{DS} = 6\text{ A}, T_J = 125^{\circ}\text{C}$		151		
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_{DS} = 19.5\text{ mA}, T_J = 25^{\circ}\text{C}$	1.2	1.6	2.5	V
		$V_{DS} = V_{GS}, I_{DS} = 19.5\text{ mA}, T_J = 125^{\circ}\text{C}$		1.5		

DYNAMIC CHARACTERISTICS

Input Capacitance	C_{ISS}	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, f = 100\text{ kHz}$		139		pF	
Output Capacitance	C_{OSS}			47			
Reverse Transfer Capacitance	C_{RSS}			0.52			
Output Capacitance, Energy Related	$C_{OSS(ER)}$	$V_{DS} = 0\text{ V to } 400\text{ V}, V_{GS} = 0\text{ V}$		68.7		pF	
Output Capacitance, Time Related	$C_{OSS(TR)}$			90.9			
Output Charge	Q_{OSS}			36.3			nC
Output Capacitance Stored Energy	E_{OSS}			5.5			μJ
Gate Resistance	R_G	$f = 5\text{ MHz}$		7		Ω	
Gate Charge	Q_G	$V_{DS} = 400\text{ V}, I_{DS} = 6\text{ A}, V_{GS} = 0/6\text{ V}$		3.8		nC	
Gate-to-Source Charge	Q_{GS}			0.3			
Gate-to-Drain Charge	Q_{GD}			1.4			
Gate Plateau Voltage	V_{PLAT}			2.1			V

REVERSE CONDUCTION CHARACTERISTICS

Source-to-Drain Reverse Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_{SD} = 6\text{ A}$		2.4		V
Pulsed Reverse Current	$I_{SD(PULSE)}$	$V_{GS} = 6\text{ V}, t_{PULSE} = 10\text{ }\mu\text{s}$			41	A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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TYPICAL CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted)

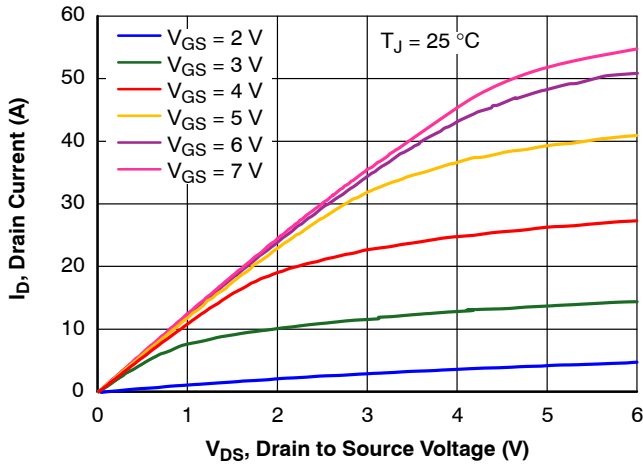


Figure 1. Output Characteristics at $T_J = 25\text{ }^\circ\text{C}$

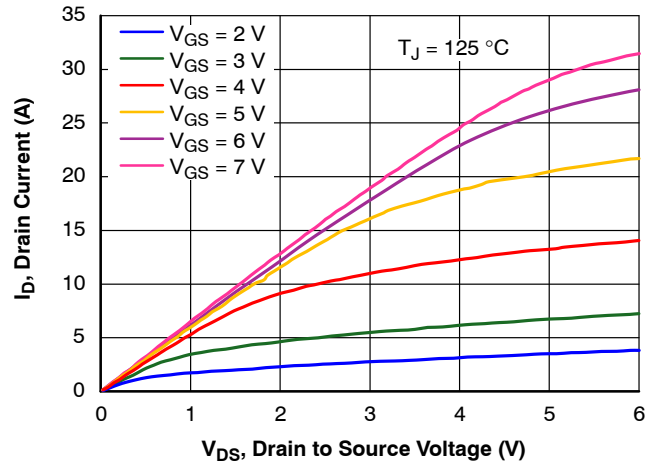


Figure 2. Output Characteristics at $T_J = 125\text{ }^\circ\text{C}$

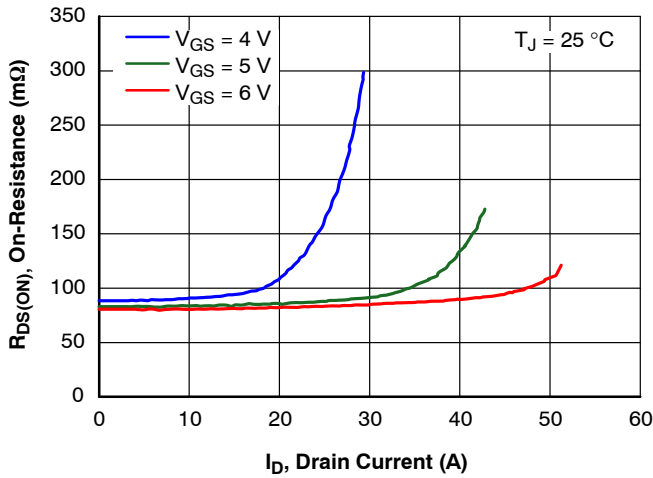


Figure 3. On-Resistance vs. Drain Current at $T_J = 25\text{ }^\circ\text{C}$

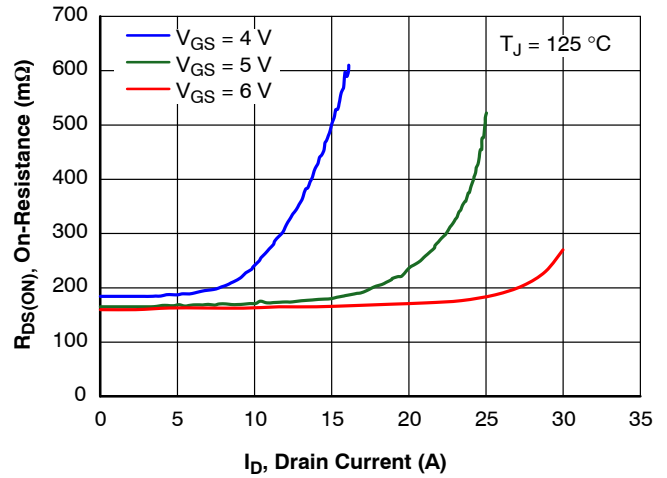


Figure 4. On-Resistance vs. Drain Current at $T_J = 125\text{ }^\circ\text{C}$

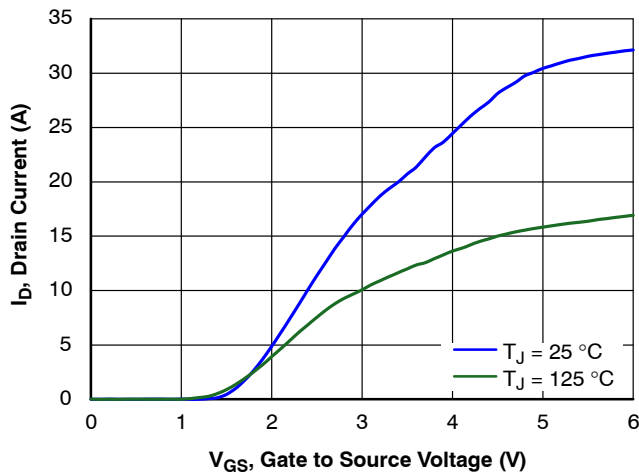


Figure 5. Transfer Characteristics at $V_{DS} = 3\text{ V}$

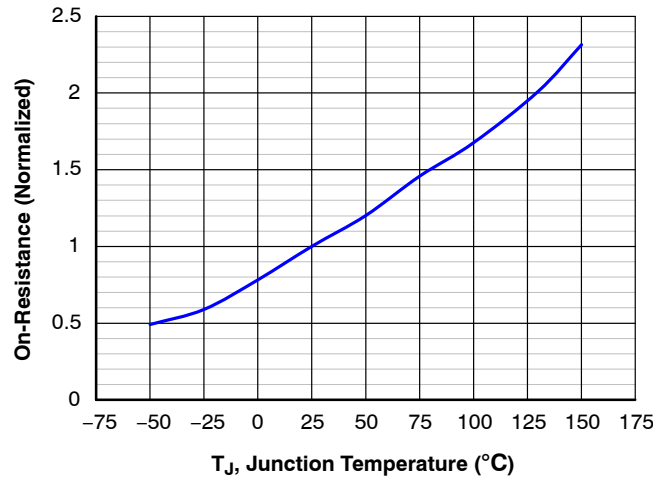


Figure 6. Normalized On-Resistance vs. Temperature at $V_{GS} = 6\text{ V}$

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TYPICAL CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified) (continued)

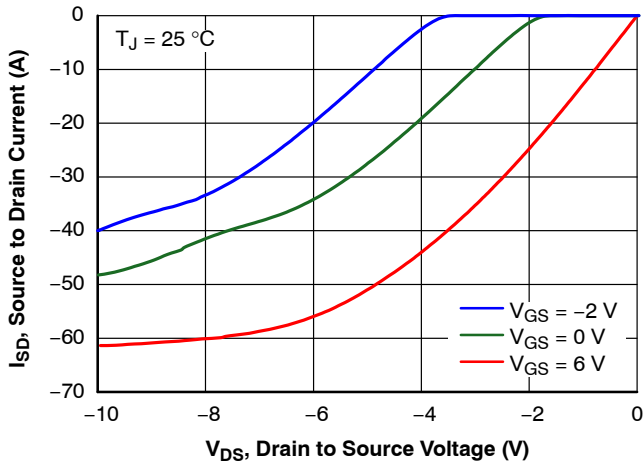


Figure 7. Reverse Conduction Characteristics at $T_J = 25\text{ }^\circ\text{C}$

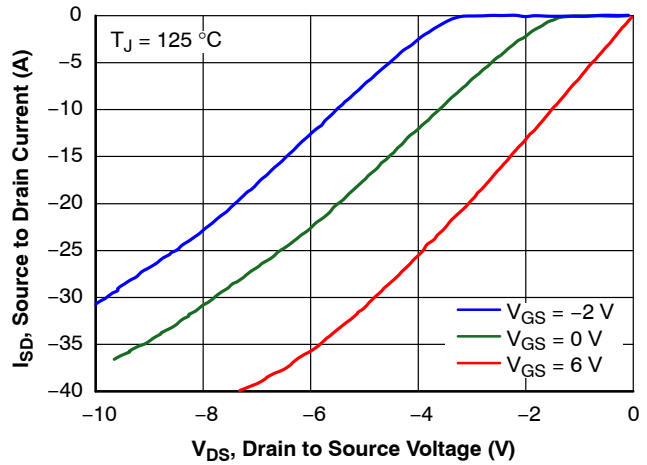


Figure 8. Reverse Conduction Characteristics at $T_J = 125\text{ }^\circ\text{C}$

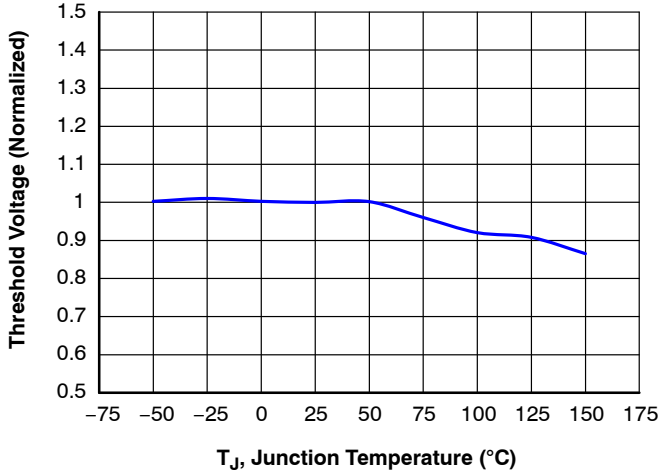


Figure 9. Normalized Threshold Voltage vs. Temperature

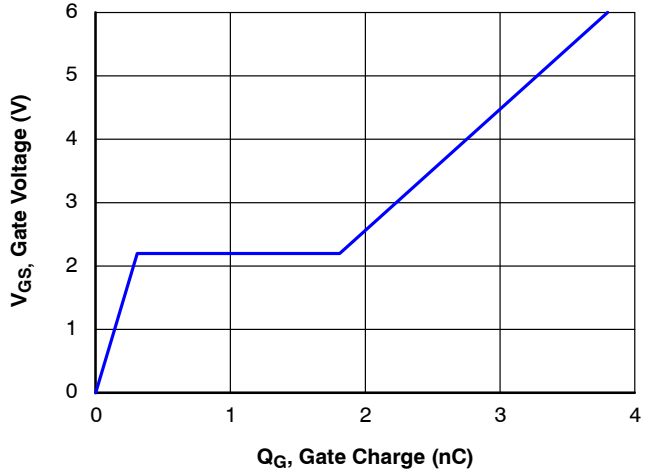


Figure 10. Gate Charge Characteristics at $I_{DS} = 20\text{ A}$

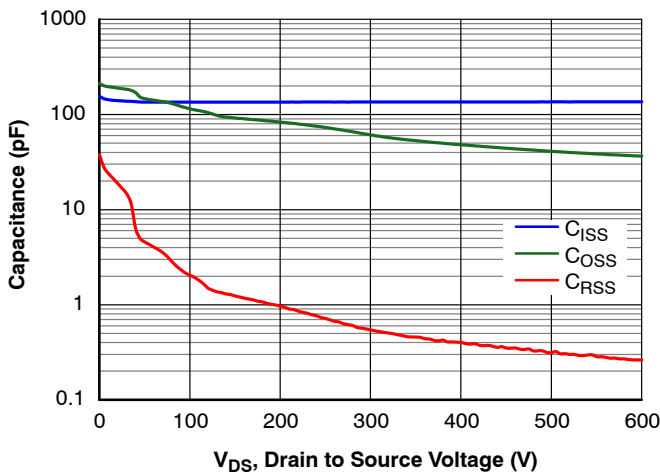


Figure 11. Capacitance Characteristics

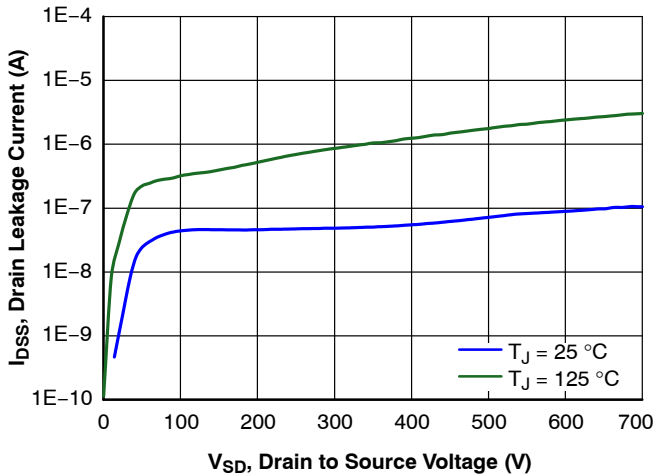


Figure 12. Drain Leakage Characteristics

NTMT100N70GN1

TYPICAL CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified) (continued)

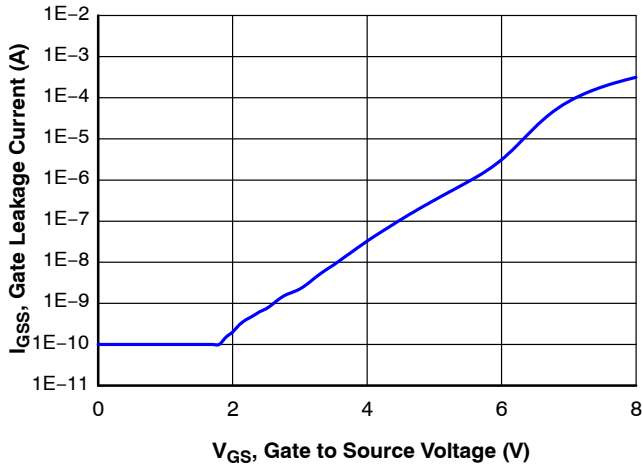


Figure 13. Gate Leakage Characteristics

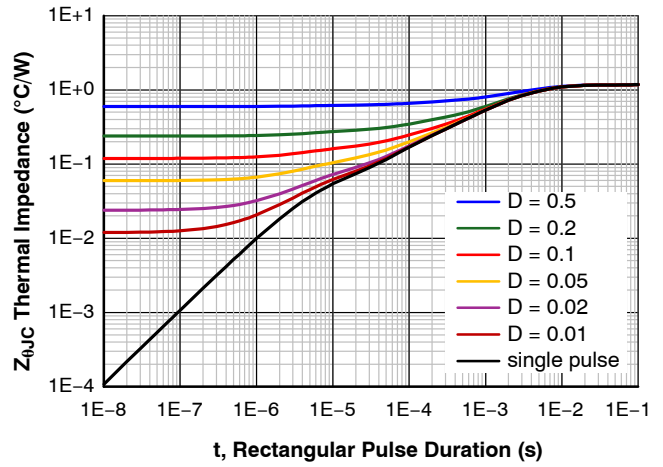


Figure 14. Transient Thermal Impedance

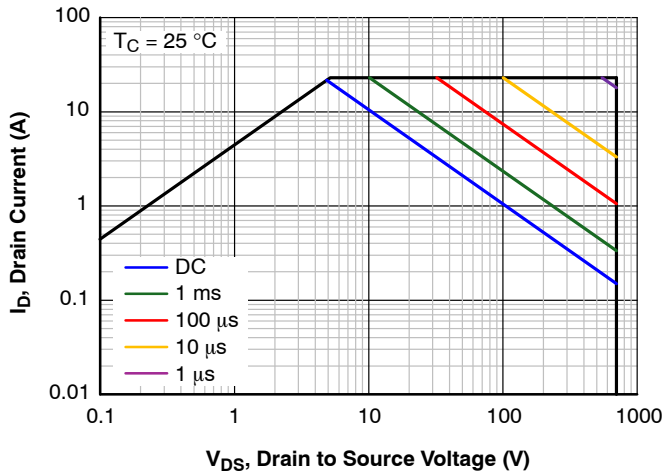


Figure 15. Safe Operating Area at $T_C = 25\text{ }^\circ\text{C}$

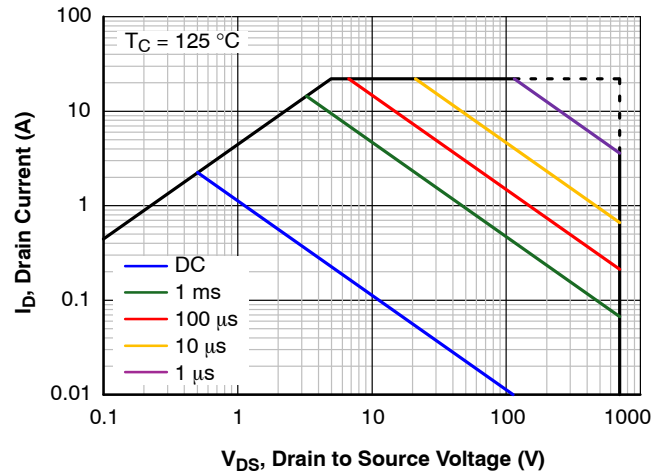
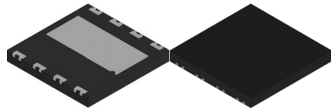


Figure 16. Safe Operating Area at $T_C = 125\text{ }^\circ\text{C}$

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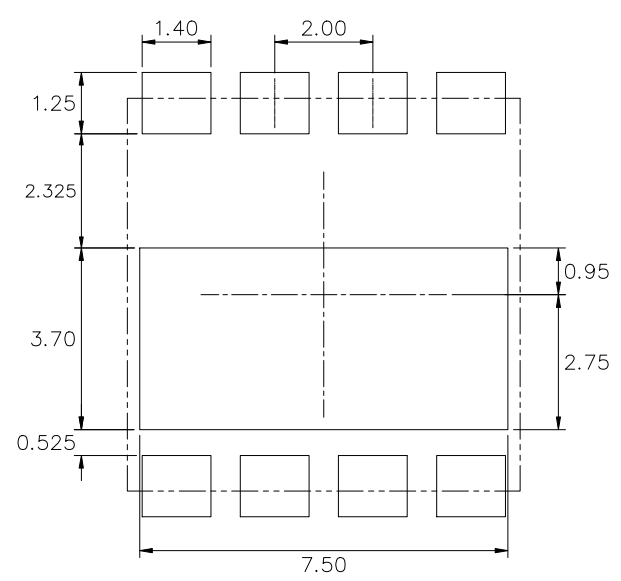
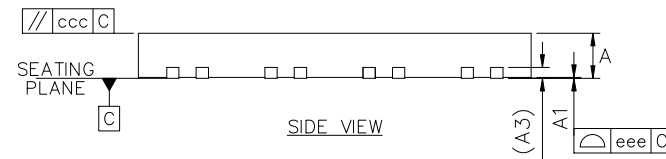
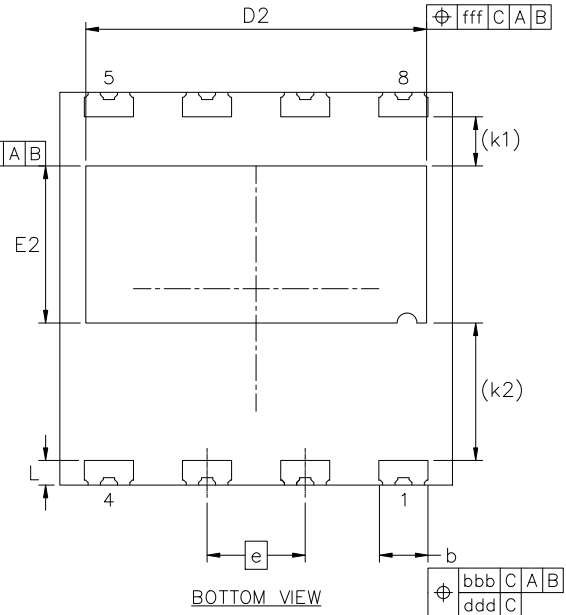
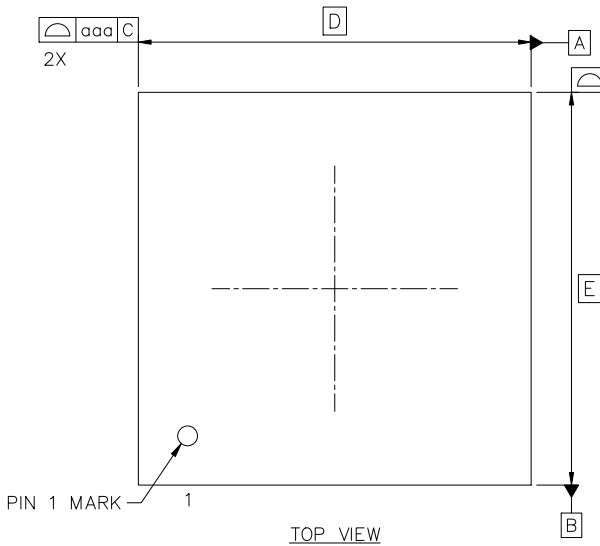
REVISION HISTORY

Revision	Description of Changes	Date
0	Initial production document release.	6/17/2026



PTFP-N9 8.00x8.00x0.90, 2.00P
CASE 522AG
ISSUE O

DATE 04 MAY 2026



- NOTES:
1. ALL DIMENSION AND TOLERANCE CONFORM TO ASME Y14.5-2018.
 2. ALL DIMENSION ARE IN MILLIMETERS
 3. DRAWING NOT TO SCALE.
 4. DIMENSION DO NOT INCLUDE MOLD PROTRUSION.
 5. PACKAGE OUTLINE EXCLUSIVE OF METAL BURR DIMENSIONS.

MILLIMETER			
SYMBOL	MIN.	NOM.	MAX.
A	0.80	0.90	1.00
A1	0.00	0.02	0.05
A3	0.203 REF.		
b	0.95	1.00	1.05
D	8.00 BSC		
D2	6.84	6.94	7.04
E	8.00 BSC		
E2	3.10	3.20	3.30
e	2.00 BSC		
k1	1.00 REF.		
k2	2.80 REF.		
L	0.40	0.50	0.60
TOLERANCE FORM & POSITION			
aaa	0.10		
bbb	0.10		
ccc	0.10		
ddd	0.05		
eee	0.10		
fff	0.10		

*For additional information on Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

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**GENERIC
MARKING DIAGRAM***



XXXX = Specific Device Code
A = Assembly Location
YY = Year
WW = Work Week
ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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